Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:
Glass and metal
Overall Length:
0.380 inches
Overall Diameter:
0.505 inches
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Press fit
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 breakover voltage, dc
Current Rating Per Characteristic:
250.00 amperes forward current, average absolute
Power Rating Per Characteristic:
500.0 milliwatts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
100.0 degrees celsius junction
Special Features:
Junction pattern arrangement: pnpn
Terminal Type And Quantity:
2 tab, solder lug and 1 case
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0